

Silicon PNP Epitaxial

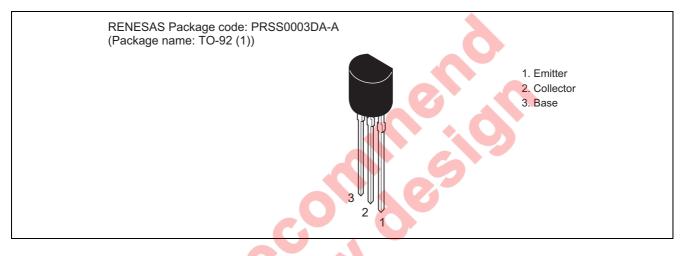
REJ03G0640-0200 (Previous ADE-208-1012) Rev.2.00 Aug.10.2005

2500

Application

- Low frequency low noise amplifier
- Complementary pair with 2SC2855 and 2SC2856

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Rating	Unit
Collector to base voltage	V _{CBO}	-90	V
Collector to emitter voltage	V _{CEO}	-90	V
Emitter to base voltage	V _{EBO}	-5	V
Collector current	Ι _C	-100	mA
Emitter current	Ι _Ε	100	mA
Collector power dissipation	Pc	400	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C



Electrical Characteristics

 $(Ta = 25^{\circ}C)$

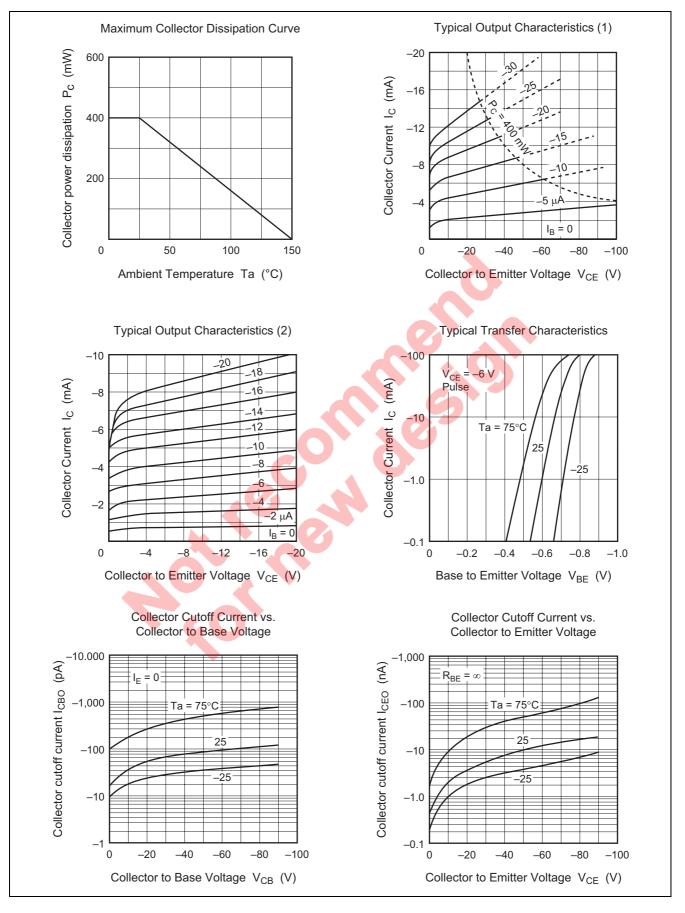
		2SA1190				
ltem	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	-90		_	V	$I_{\rm C} = -10 \ \mu A, \ I_{\rm E} = 0$
Collector to emitter breakdown voltage	V _{(BR)CEO}	-90		_	V	$I_C = -1 \text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	V _{(BR)EBO}	-5		_	V	$I_E = -10 \ \mu A, \ I_C = 0$
Collector cutoff current	I _{CBO}			-0.1	μA	$V_{CB} = -70 \text{ V}, I_E = 0$
Emitter cutoff current	I _{EBO}	_	_	-0.1	μΑ	$V_{EB} = -2 V, I_C = 0$
DC current trnsfer ratio	h _{FE} * ¹	250	—	800		$V_{CE} = -12 V,$ $I_{C} = -2 mA^{*2}$
Collector to emitter saturation voltage	V _{CE(sat)}	—	-0.05	-0.15	V	$I_{C} = -10 \text{ mA},$ $I_{B} = -1 \text{ mA}^{*2}$
Base to emitter saturation voltage	V _{BE(sat)}		-0.7	-1.0	V	
Gain bandwidth product	f⊤	—	130	—	MHz	$V_{CE} = -6 V,$ $I_{C} = -10 mA$
Collector output capacitance	Cob	—	3.2	-	pF	$V_{CB} = -10 \text{ V}, \text{ I}_{E} = 0,$ f = 1 MHz
Noise figure	NF		0.15	1.5	dB	$V_{CE} = -6 V,$ $I_{C} = -0.1 mA,$ $R_{g} = 10 k\Omega$ f = 1 kHz
			0.2	2.0	dB	$V_{CE} = -6 V,$ $I_C = -0.1 mA,$ $R_g = 10 kΩ$ f = 10 Hz
Noise voltage referred to input	en	e	0.7		nV/ √Hz	$V_{CB} = -6 V$, $I_{C} = -10 mA$, Rg = 0, f = 1 kHz

Notes: 1. The 2SA1190 and 2SA1191 are grouped by hreas follows.

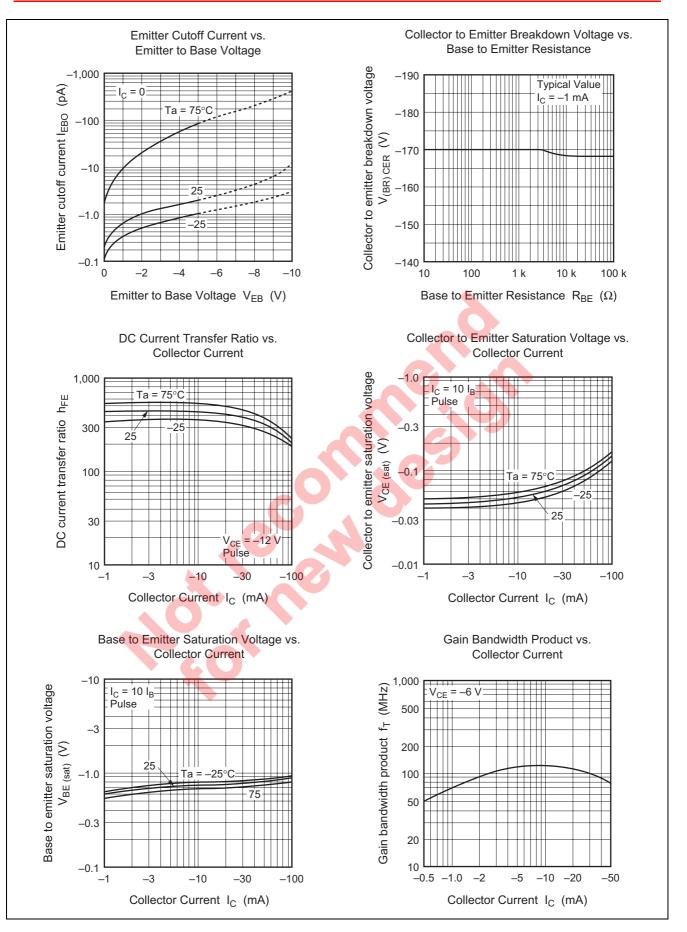
D	E	
250 to 500	400 to 800	
		\mathbf{O}
		X



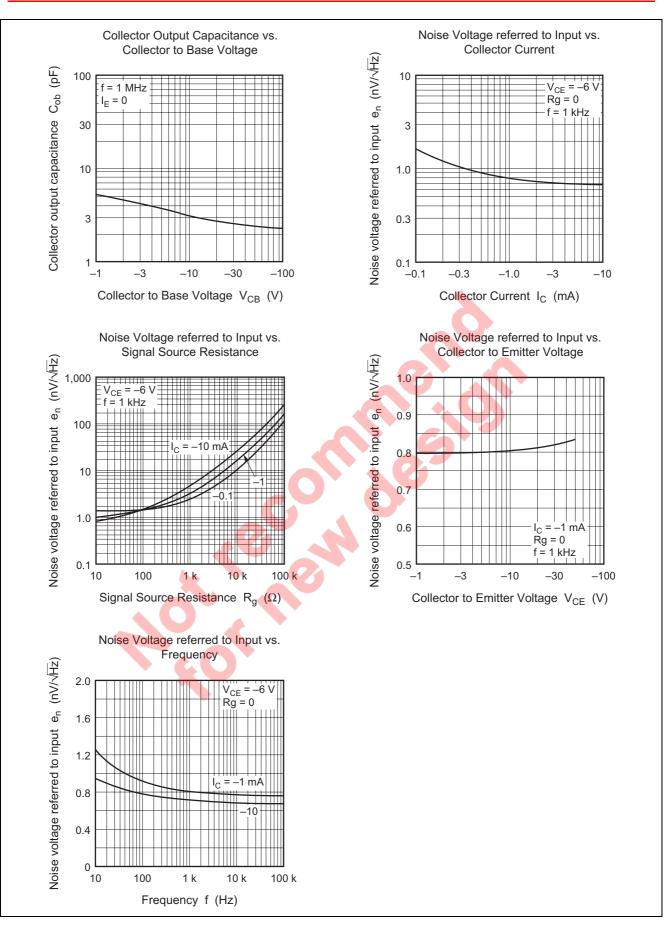
Main Characteristics





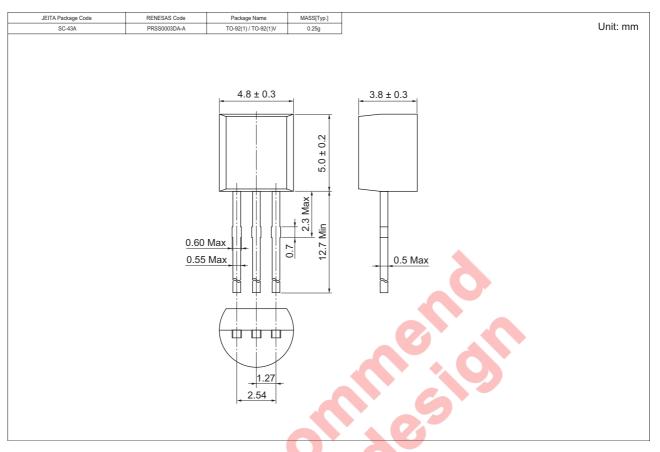








Package Dimensions



Ordering Information

Part Name		Quantity	Shipping Container	
2SA1190DTZ-E	2500		Hold Box, Radial Taping	
2SA1190ETZ-E				

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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